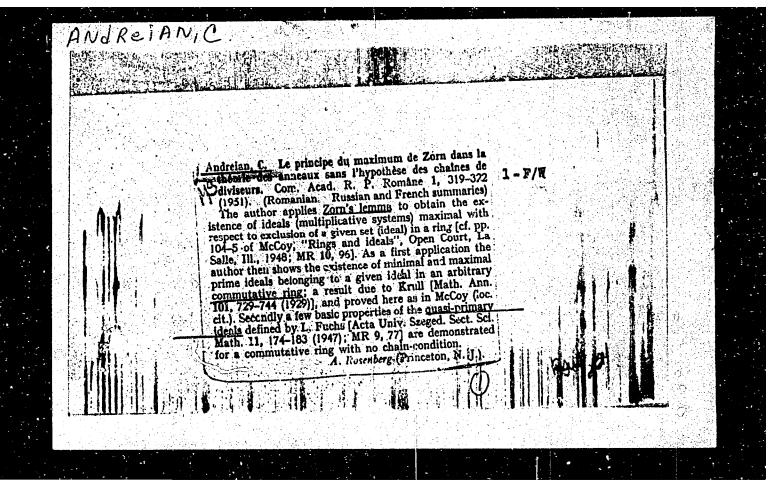


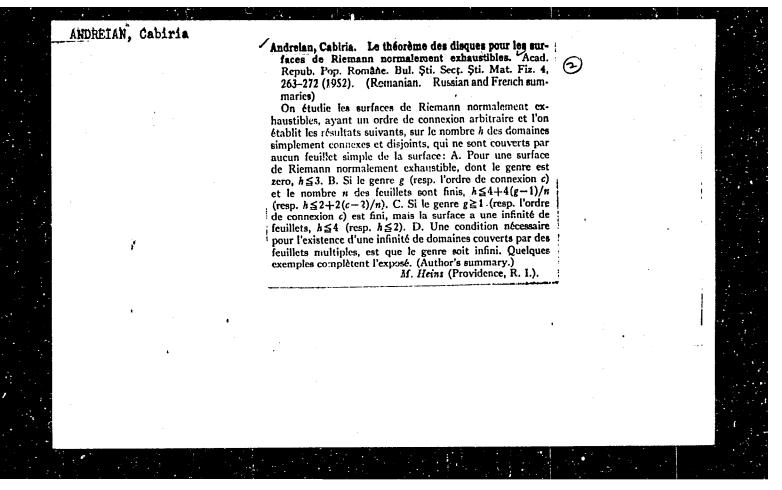
SHIROKOV, Yu.G.; ANDREICHEV, V.N.; KIRILLOV, I.P.

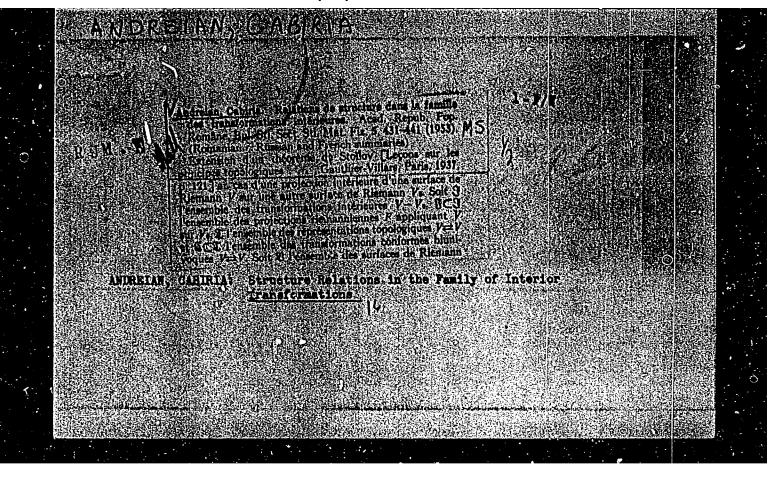
Dielectric constant and dielectric losses of nickel oxide and nickel oxide-aluminum oxide. Izv. vys. ucheb. zav., khim i khim tekh. 7 no.5:774-781 '64 (MIRA 18:1)

l. Kafedra tekhnologii neorganicheskikh veshchestv Ivanovskogo khimiko-tekhnologicheskogo instituta.

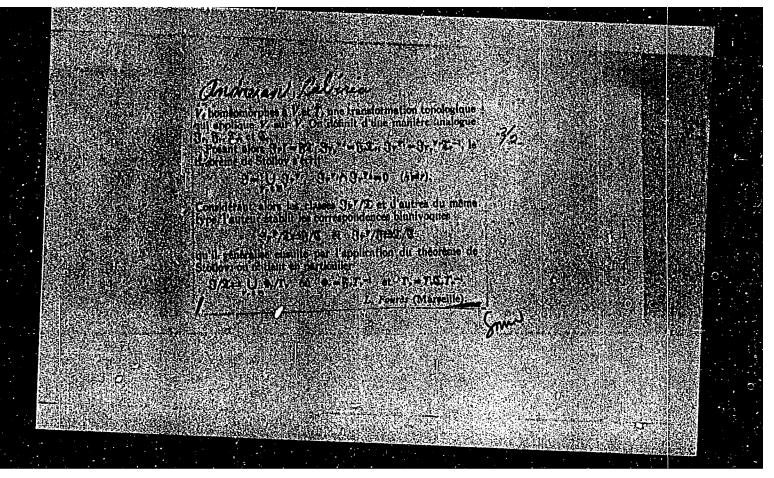
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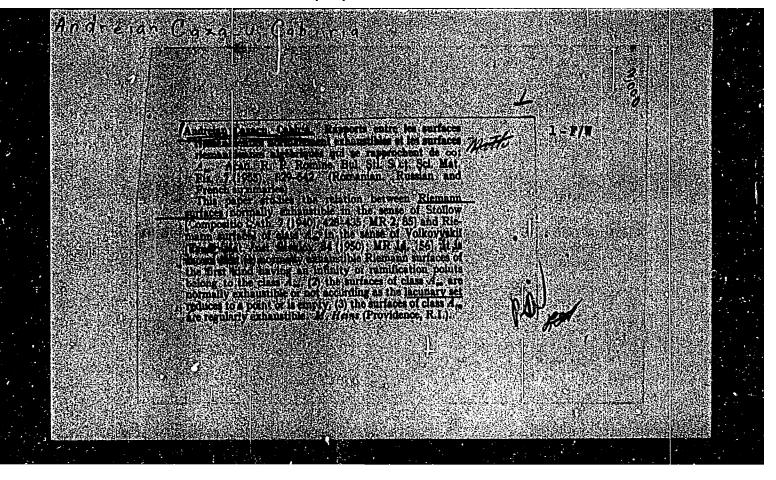


ANDREIAN CAZACU, C.

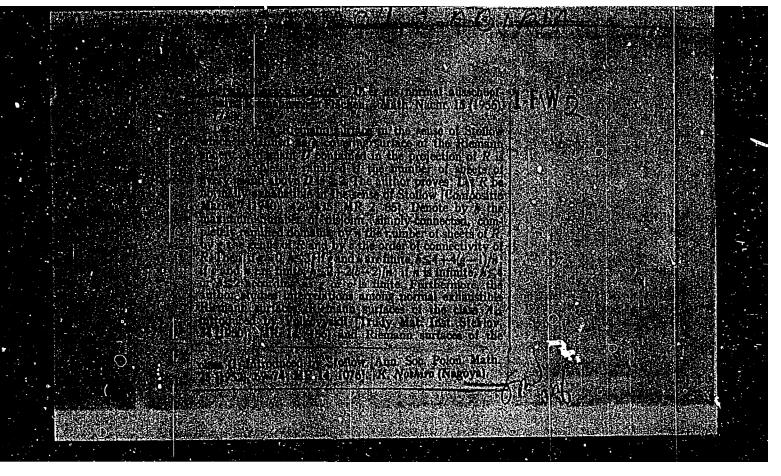
Iversen's theorem for Riemann surfaces normally exhaustible. p. 1145. COMUNICARILE. Bucuresti. Vol. 5, no. 8, Aug. 1955.

SOURCE:

East European Accessions List (EEAL) Library of Congress Vol. 5, No. 7, July 1956.



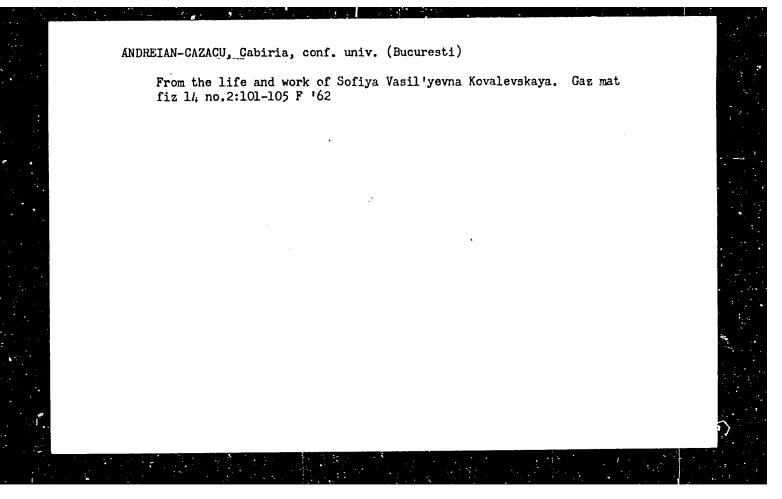
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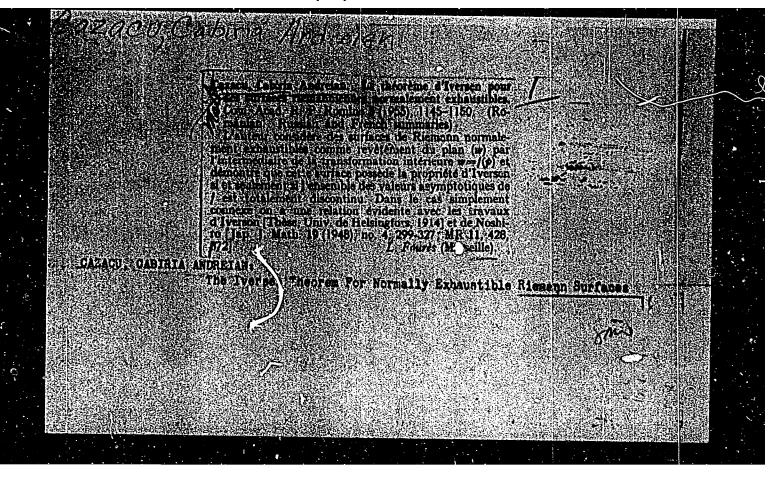


ANDREIAN CAZACU, Cabiria

On a formula of S. Stoilow. Rev math pures 5 no.1:59-74 '60.
(EEAI 10:9)

(Riemann surfaces) (Topology)





8/044/63/000/002/010/050 A060/A126 Andreian, Cazacu, Cabiria **AUTHOR:** On the problem of type TITLE: MERIODICAL: Referativnyy zhurmal, Matematika, no. 2, 1963, 25 - 26, abstract 2B110 (An. Univ. C. I. Pathon. Ser. stiint natur., 1959, no. 22, 23 - 37; Rumanian; summaries in Russian, French) M.A. Lavrent'yev's result is known: the quasiconformal mapping of the finite plane $z = r \exp(i\theta)$ with characteristic p(z) retains the parabolic type, provided the integral diverges, where $p(r) = \max_{|z|=r} p(z)$. The author, generalizing a result of R.J. Wille (Indagationes Math., 1947, v. 9, no. 4, 415 - 419), proves that for certain special classes of quasiconformal mappings this integral criterion can be im-Card 1/3

On the problem of type

S/044/63/000/002/010/050 A060/A126

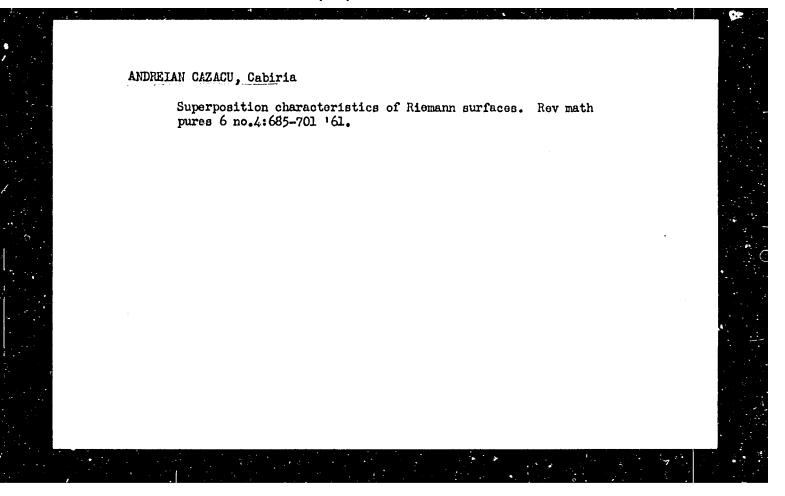
proved. Let $\{c_{\lambda}\}$ be the family of level lines of a continuously differentiable function $\lambda = \lambda(x, y)$, $\lambda \in (\lambda_0, \infty)$ (if $\lambda' < \lambda''$, then c_{λ} ! lies within c_{λ} ! and as $\lambda \to \infty$, c_{λ} contracts to the point $z = \infty$), filling the domain $\delta \subset (|z| < \infty)$, z = x + iy. Orthogonal to $\{c_{\lambda}\}$ is the family $\{\gamma_{\lambda}\}$ of level lines of the continuously differentiable function t = t(x, y), $t \in [a, b]$, $\gamma_a = \gamma_b$, where λ and t form a system of curvilinear coordinates in δ . With respect to $\{c_{\lambda}\}$ and $\{\gamma_{t}\}$ it is assumed that

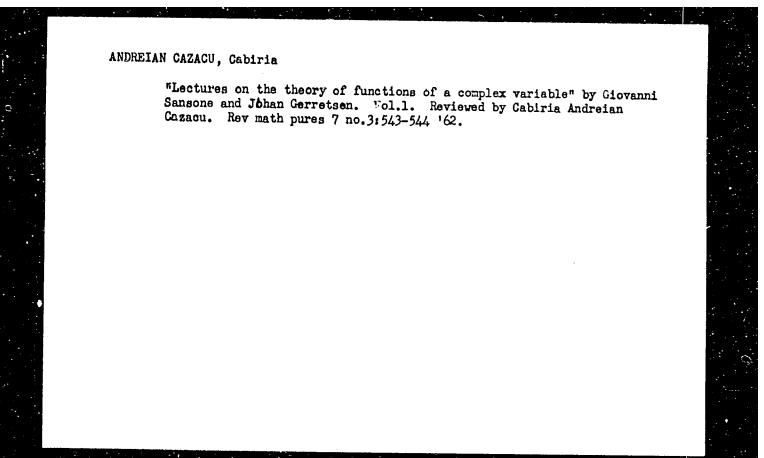
 $\frac{|\operatorname{grad} \lambda|}{|\operatorname{grad} t|} = F(\lambda) \cdot G(t).$

where $F(\lambda) \ge 0$ and $G(t) \ge 0$. Let $\{C_A\}$ and $\{\Gamma_T\}$ be analogous families in the Z plane covering the domain Δ . One constructs a quasiconformal mapping δ on Δ in the form $A = g(\lambda)$ and $T = h(\lambda, t)$ with one pair of characteristics $p(z) = p(\lambda)$ and $C(z) = C(\lambda)$ for $z \in C_\lambda$, where C(z) is the angle between the tangent to C_λ and the major semiaxis of an infinitesimally small ellipse centered at the point z. Such a mapping Z = f(z) exists when certain conditions are fulfilled. In order that Z = f(z) retain the parabolic type it is necessary and sufficient that the integral

Card 2/3

On the problem	n of type	8/044/63/000/002/010/050 A060/A126	
	$\int_{0}^{\infty} \frac{p(\lambda)}{\cos^{2}\alpha(\lambda) + p^{2}(\lambda) \sin^{2}\alpha}$	$\frac{d\lambda}{d(\lambda)} \frac{d\lambda}{f(\lambda)}$	
diverge. The	applications of this result to the nated.	problem of a Riemann type sur-	. a
[Abstracter's	note: Complete translation]	D.B. Potyagaylo	
Card 3/3			





ARESTEANU, L., dr.; NICOLAU, Silvia, chim.; RUBINGHER, Lidia, chim.; ANDREIAS, Cornelia, stud.; DULCEANU, Icsefina, asist. med.

Apropos of coexisting pancreatic disease in patients with chronic hepatitis and post-hepatitis liver cirrhosis. Value of the combined pancreozymin and secretin test. Med. intern. (Bucur.) 17 no.9:1111-1118 S 165.

1. Lucrare efectuata in Clinica medicala de semiologie, Spitalul "Dr. Carol Davila", Institutul medico farmaceutic, Bucuresti (director: conf. S. Ciorpaciu).

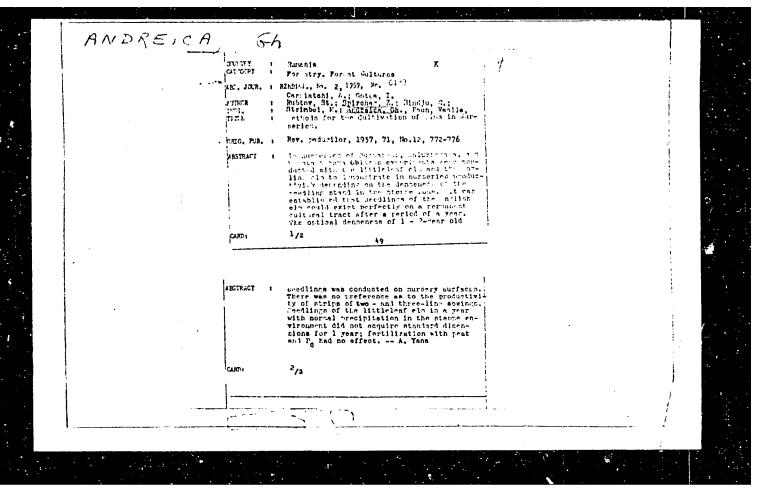
BARBER, Celia; EUSTATZIOU, Silvia; ANDREICA, Angela, collaborateur technique

A contribution to the study of the biology of Klebsiella. III. Chemical and immunological study of polysaccharides isolated from 2 capsulated strains and their noncapsulated mutants. Arch. Roum. path. exp. microbiol. 20 no.1:103-113 Mr ¹61.

1. Travail de l'Institut "Dr. I. Cantacuzino" - Service de Biochimie Generale.

(KLEBSIELLA chem) (POLYSACCHARIDES chem)

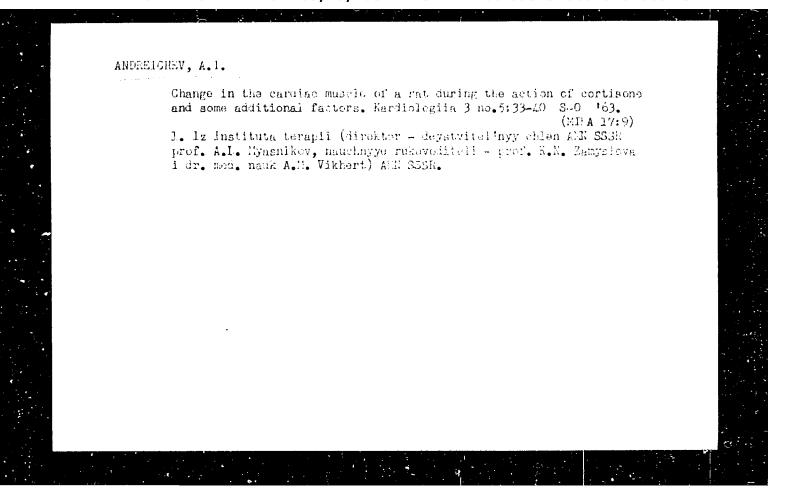
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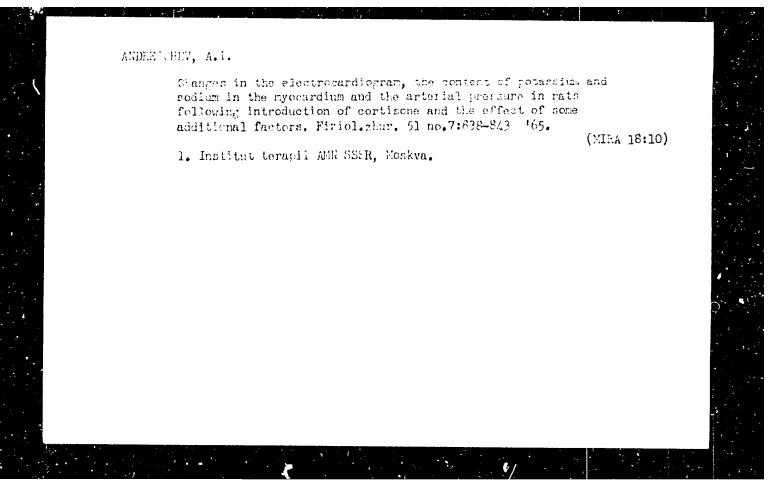


IACOBESCU, D.; AMDREIGA, V.

Open way for plastic materials in constructions. Constructions. Buc 15 no.700;2 8 Je '63.

1. Inginer-sef al fabricii "Horia, si Crisan", Turda (for Iacobescu).





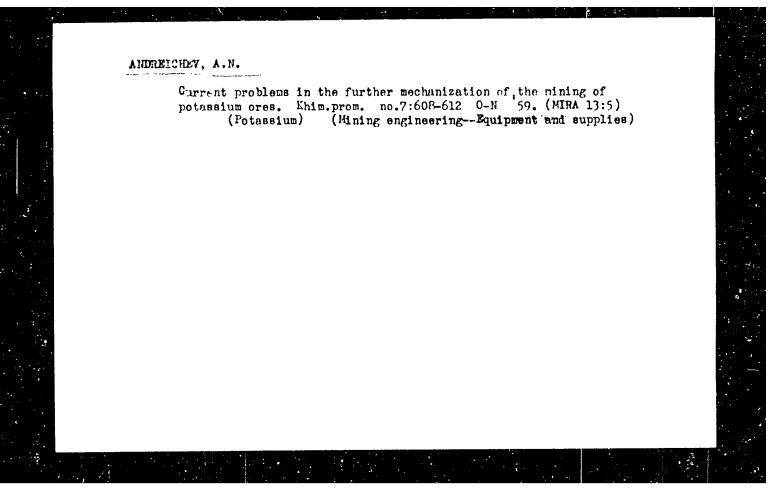
SOV/64-59-5-14/28 5(1), 2(1) Andreichev, A. N. AUTHOR: On the Use of Explosives in the Potash Industry TITLE: Khimicheskaya promyshlennost', 1959, Nr 5, pp 418-419 (USSR) PERIODICAL: Unsafe explosives are applied to potash mines in USSR (except ABSTRACT: for the mining of carnallite). The necessity of using safe explosives for potash mining is discussed (in analogy to explosives used for coal mining). It is pointed out that clouds of dust occurring in explosions in potash mines immediately extinguish the arising flame with their inert property, so that also under formation of explosive gases an inflammation would be located. In Eastern Germany, unsafe explosives, partly containing also nitrocompounds (Table 2, properties of these explosives), were also applied to potash mines (Table 1). The explosive effect of donarites and gelatin-donarites is about 1.5 times larger than that of the safe explosives, that are produced in USSR (Ref 2) and equals the effect of ammonites Nr 6 and Nr 7. The addition of inert materials to explosives (for their safety) extremely diminishes the explosive effect and causes the reduction of the mining results, especially in Card 1/2

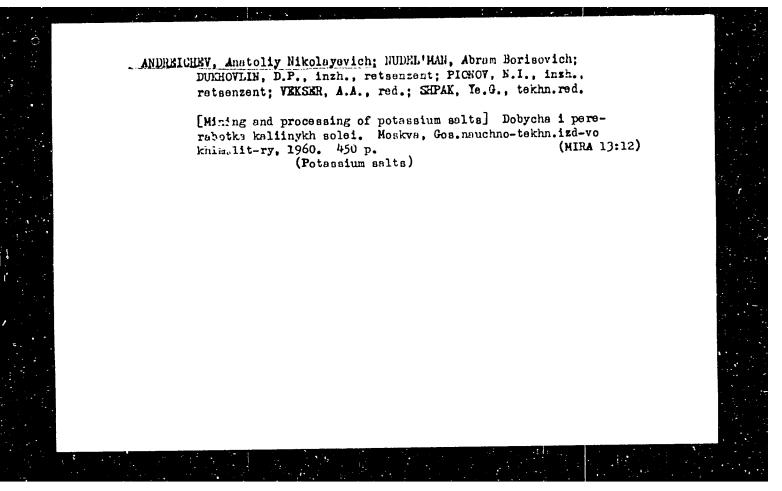
On the Use of Explosives in the Potash Industry

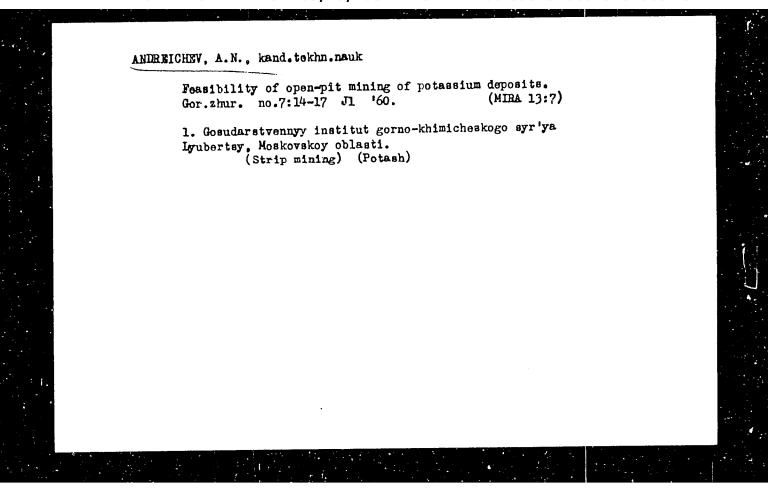
SOV/64-59-5-14/28

tough stone like sylvite and rock salt. The high explosive power of the dynamites is of main importance in the mining of carnallite. The use of safe explosives may cause a necessary diminution of the explosive effect, a process, that may also be obtained by reduction of the loading (with unsafe explosives). Considerations admit the statement that the application of safe explosives to potash salt mines is improper. Explosives, manufactured in USSR under the trade name rock ammonites, are of special interest, because their explosive effect and their high explosive power are considerably larger than those of ammonium nitrate explosive (Table 3, data of the first-mentioned explosives with type designations). There are 3 tables and 2 references, 1 of which is Soviet.

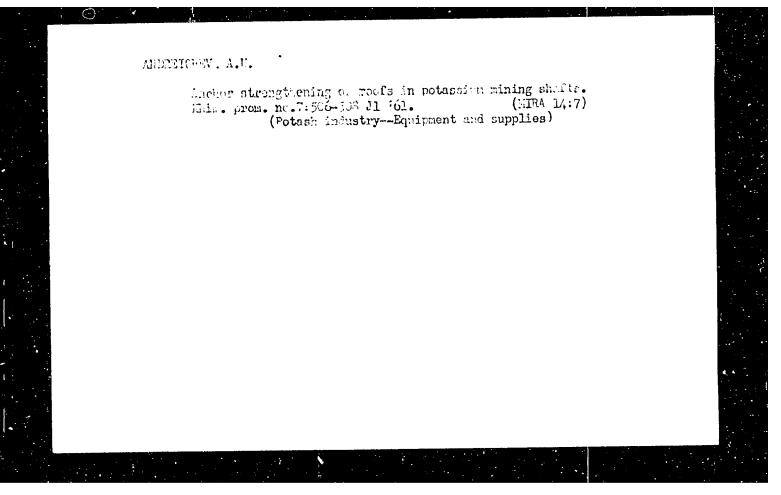
Card 2/2

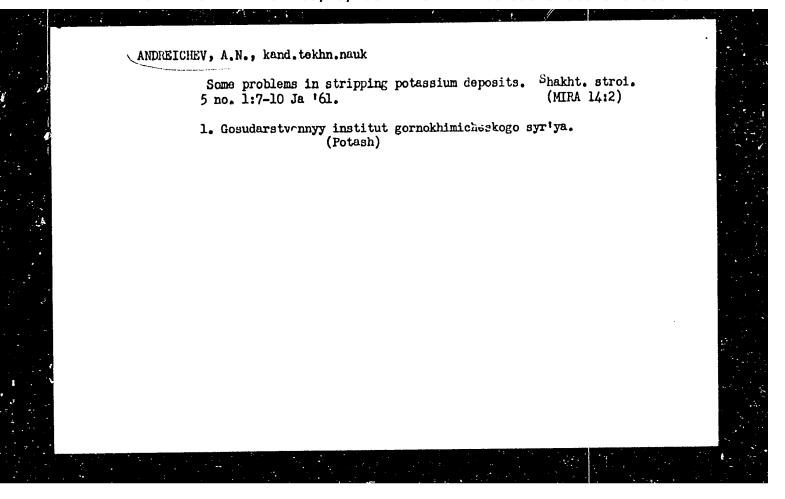


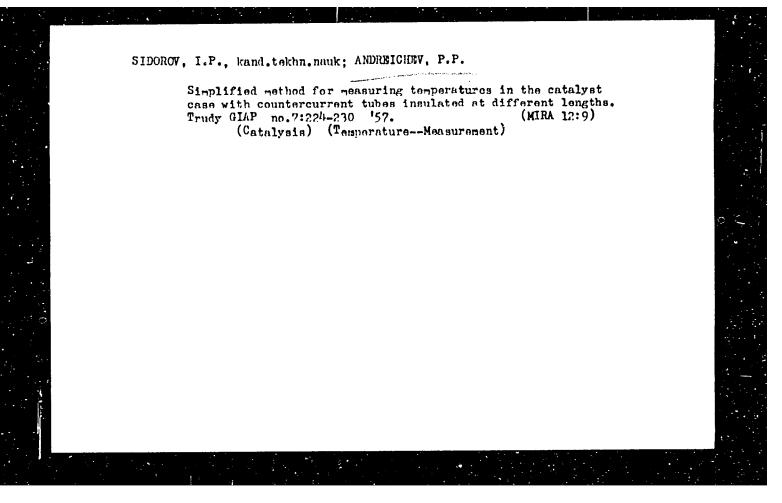




ANDREICHEV, A.N., kand.tekhn.nauk Efficient utilization of the Starobin potassium deposit. Khim. prom. no.6:405-409 Je '61. 1. Gosudarstvennyy nauchno-issledovatel'skiy institut gornokhimicheskogo syr'ya. (Starobin—Potassium)







SIDOROV, I.P.; KAZARNOVSKAYA, D.B.; ANDREICHEV, P.P.

Recirculation flow method for studying the kinetics of heterogeneous catalytic reactions at high pressures. Kin.i kat. 3 no.4:523-526 Jl-Ag '62. (hTRA 15:8)

1. Gosudarstvennyy nauchno-iscledovatel'skiy institut azotnoy promyshlennosti. (Catalysis)

ACCESSIONNR: APSO1783

S/0153/64/007/008/0774/0761

AUTHOR: Shirokov, Yu. G. Andreichev, V. N.; Kirillov, I. P.;

TITLE: Dielectric permeability and dielectric losses of NiO and NiO-Al₂O₃

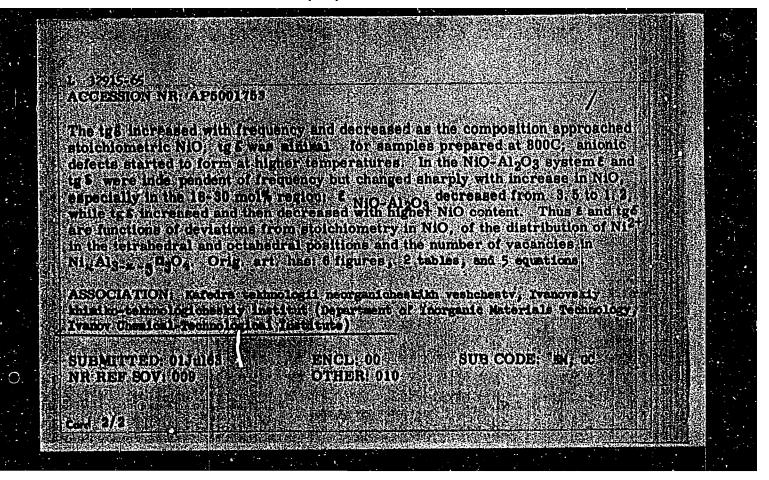
SOURCE: IVUZ. Khimiya I khimicheeksya teknologiya, v. T. no. 5, 1964.

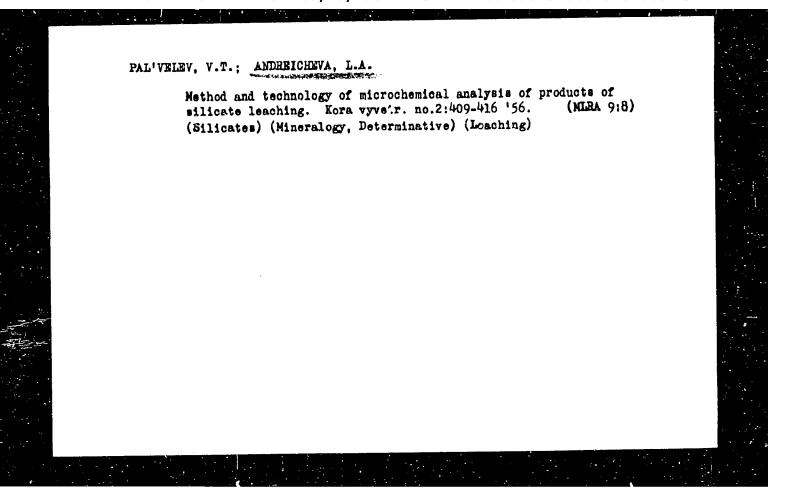
TOTALE: Objective permeability and dielectric losses of NiO and NiO-Al₂O₃

SOURCE: IVUZ. Khimiya I khimicheeksya teknologiya, v. T. no. 5, 1964.

TOTALE: Objective permeability and the tangent of the angle of dielectric permeability. All listerio loss

ABSTRACT: The dielectric permeability and the tangent of the angle of dielectric loss of the confidence of the confidence of the loss of the sequence of the loss of the loss of the language of the loss of the loss of the loss of the loss of the language of the language of the loss of the language of the lang





ORAHOVATS, D., acad.; GLAVCHEVA, ..; ANDREICHEVA, M:

A study of certain laws governing the release of proteins into the gastric juice and the part played by the nervous system in this process. Rumanian M Rev. no.1:205-214 Ja-Mr '61.

1. The Institute of Experimental Medicine of the Academy of Sciences, Bulgaria.

(PROTEINS matabolism) (GASTRIC JUICE chemistry)

(NERVOUS SYSTEM physiology)

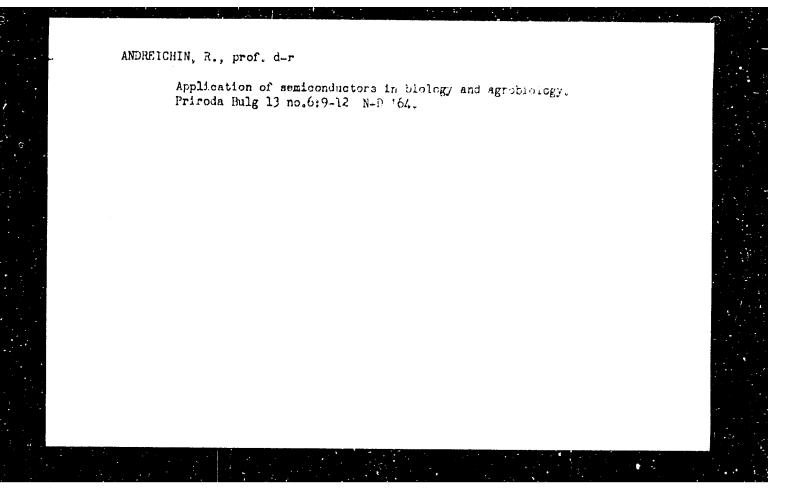
ANDREICHEVA, Ning Alekseyevna; SENKÖV, Fedor Vasil'yevich;

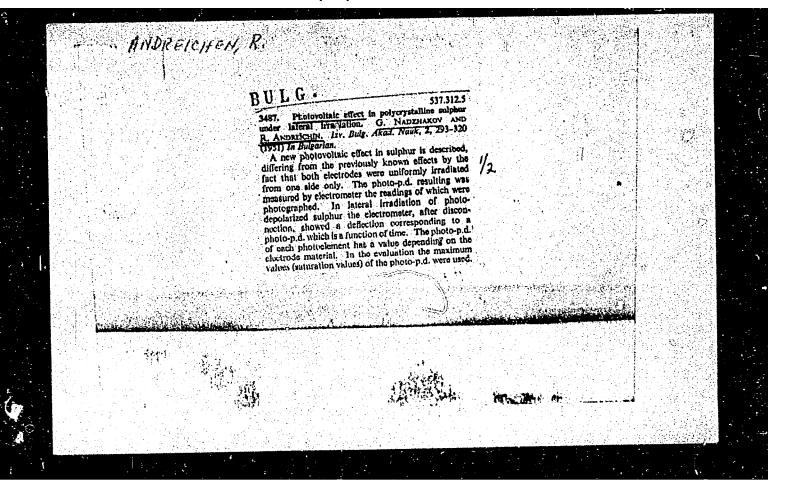
RYAZANTSEVA, L.I., red.; KASIMOV, D.Ya., tekhn. red.

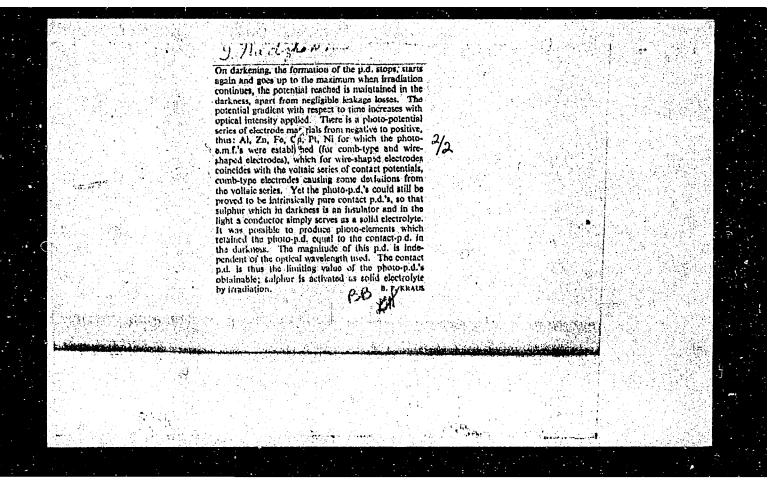
[Protecting wood from rot; assistance for the rural builder] Zashchita drevesiny ot gnieniia; v pomoshch' sel'skomu stroiteliu. Moskva, Gosstroitzdat, 1963. 62 p.

(MIRA 16:5)

(Wood--Preservation)







ANDREICHEV, A.N., kand. tekhn. nauk

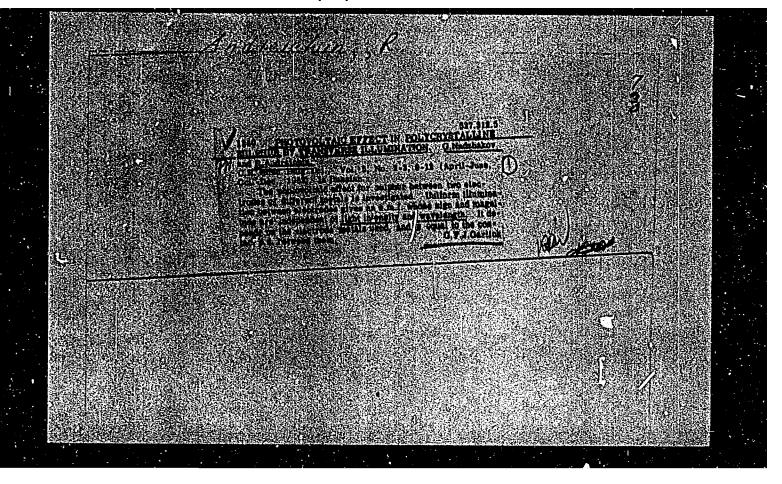
What kind of tubing is needed for the shafts of potash mines.
Shakht. strol. 5 no.9:11-13 S '61. (MIRA 16:7)

1. Gosudarstvennyy institut gornokhimicheskogo syr'ya.

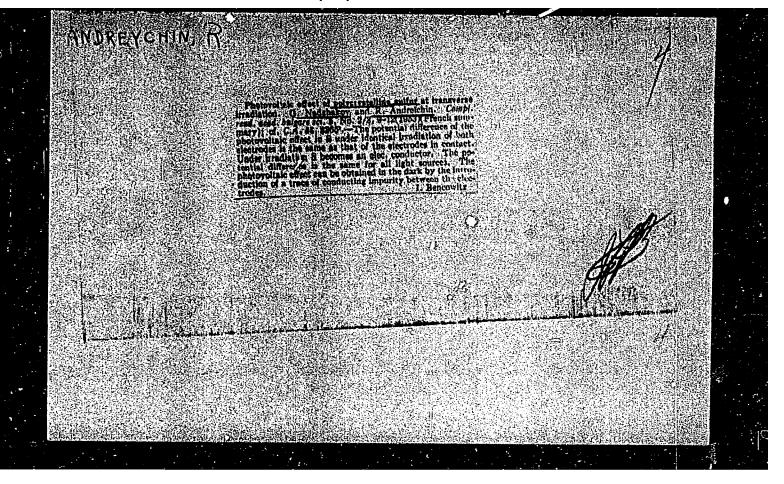
(Potash) (Mine timbering)

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THE RESERVE OF THE PARTY OF THE	E) Ref. zh. Khimi	San			X	
TITLE	On Simple explo	N.; Kushnarev, D.				
			ti, v. 6, no. 8, 19			or hope
TRANSI Gases Simple ammoni chamic and du	ATIN: A comparise in the products of explosives: igds to No.6. The author al enterprises with st. V. Zhilin	on is given of exp an explosion, and unites, aquatol, gr	gramulite, zernogo losive properties, the cost of blasti anulite AS and zern ow the use of simpl mines which are da	the amount of t ng operations u ogonulite 80/20	oxio sing , and	
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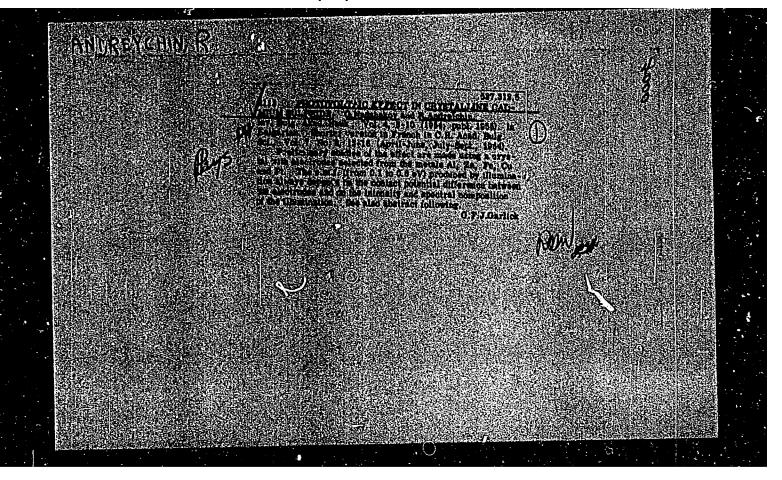
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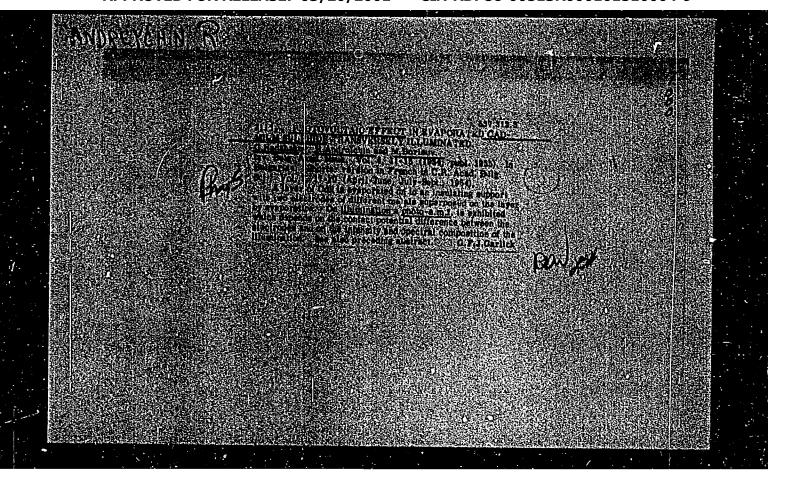
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BULGARIA/Electricity - Semiconductors

G-3

Abs Jour : Ref Zhur - Fizika, No 12, 1958, No 27880

: Nadjakov G., Andrejtschin R., Balabanov St., Stanislavova J. Author

: Physics Institute, Bulgarian Academy of Sciences, Sofia, Inst

Bulgaria.

: Comparative Investigations of the Longitudinal and Trans-Title

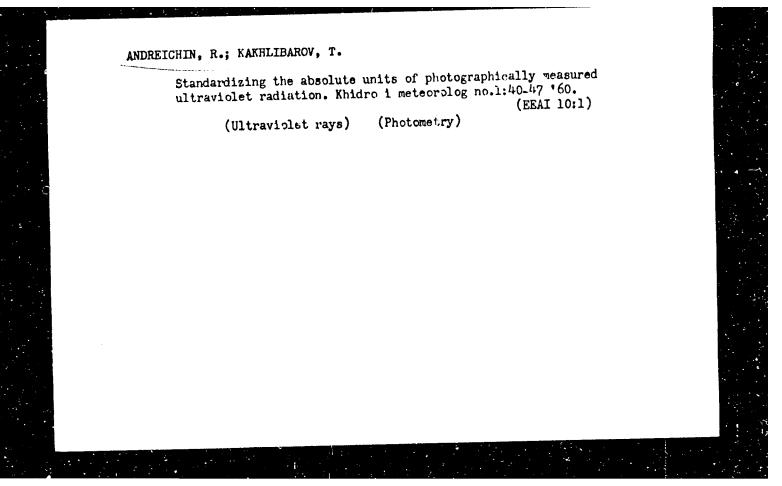
verse Photovoltaic Effects in Samples of Cadmium Sulfide

Obtained by Evaporation.

Orig Pub : Dokl. Bolg. AN., 1957, 10, No 4, 277-280

Abstract: The authors have investigated the principal characteristics of the photovoltaic offect in specimens of CdS, obtained by evaporation, with different (Al and Au) electrodes in the case of longitudinal and transverse illumination (relative to the electrodes). Data are given on the dependence of the photo emf and the photocurrent i on the intensity I. It is shown that in most cases the photovoltaic effect has the same features: i depends on I linearly, and the dependence of E on I is described by a curve that has saturation. No rectifying effect was observed. In all cases the photo

enf is of the purely barrier type. : 1/1 Card



9,4179(1114,1137) 26, 1512 31l₁27 B/502/60/008/000/001/003 D260/D304

AUTHOR:

Nadzhakov, G., and Andreychin, R.

TITLE:

Contact-potential photovoltaic effect

SOURCE:

Bulgarska akademiya na naukite. Fizicheski institut. Izvestiya na fizicheskiya institut s ANEB, v. 8,

1960, 5-15

TEXT: The authors discovered and studied a phenomenon which consists of the appearance of an electromotive force and flow of current when the setting in motion of the charge carriers released by the light is due to the contact potential difference between the electrodes. This phenomenon is called contact potential - photovoltaic effect (CPPE). The goal of the article is to summarize the main characteristics of the effect and to establish its place among the other known photovoltaic effects. This effect is demonstrated in its purest form in semi-conductors which have two ohmic contacts of different metals deposited on them, and when illumination is transversal and absolutely uniform along the entire layer, it is

Card 1/5

31427 B/502/60/008/000/001/003 D260/D304

Contact-potential photovoltaic ...

said that the effect can exist simultaneously with the remaining types of photovoltaic phenomena, as well as independently. No photovoltaic effect is to be observed with electrodes of one and the same metal whereas with electrodes of two different metals, the polarity of the photoelectromotive force follows exactly the sign of the contact potential difference between the electrodes. It has been demonstrated for photoelements of sulphur that the photoelectromotive force is exactly equal in sign and value to the contact potential difference between the electrodes, and that it depends neither on the intensity nor on the spectral composition of the light. In the case of semi-conductors, the sign of the electromotive force also follows the polarity of the contact potential difference between the electrodes; its value depends on the intensity of the light, showing a tendency to approximate a saturated value equal or close to the contact potential difference between the electrodes. The dependence of the current on the intensity of light is in most cases close to linear. Photoelements of evaporated films of CdS, PbSm Ag2S and of crystals of CdS, NaCl and PbS were inve-

Card 2/5

Contact-potential photovoltaic ...

31427 B/502/60/008/000/001/003 D260/D304

stigated. In the case of thin layers of CdS the effect does not depend on the direction or manner of illumination. Tests on transversal and longitudinal illumination are illustrated graphically. Detailed investigations on the contacts between the metal and the semi-conductor indicate that three types of photoelements are obtained, although the technology is not yet standardized sufficiently: (1) With both ohmic contacts, (2) with variator contacts, and (3) with rectifying contacts. All three types of photoelements prove that the CPPE is independent of the type of contacts. The independence of the CPPE from the structural one has been demonstrated in the case of PbS and the photoelements obtained show only the first one. In semi-conductors of purely ionic or mixed conductivity it was established that in cases of different electrodes the CPPE is added to the galvanic current existing in the dark. A working hypothesis has been set up for a qualitative explanation of the phenomenon. The authors assume that the electromotive force is due to the existing contact-potential difference between the electrodes, its manifestation and flow of current occurring when the light releases suitable charge carriers in the interior of the semi-con-Card 3/5

Contact-potential photovoltaic ...

311,27 B/502/60/008/000/001/003 D260/D304

ductors, in a manner analogous to the ions obtained in the galvanic elements through electrolytic dissolution. In order to differentiate more precisely between the CPPE and the remaining simple photovoltaic effects, Tauc's classification (Ref. 21: Rev. of Modern Physics, v. 29, 1957, 308-324) was revised and a new variant suggested, namely the five simple photovoltaic effects should be situated along a circle. By strictly observing their division into barrier and non-barrier ones, contact and non-contact, the gradual transition upon a closed circle becomes apparent. In this particular instance, the CPPE effect which holds a place between the Dember effect and the photoeffect in barrier layer, bears a certain similarity to the Dember effect, in that they are both non-barrier ones, but it is not homogeneous and the electrodes play no part in the Dember effect; the CPPE depends in the first place on the electrodes and in its pure form does not depend on the nonhomogeneity of the illumination. The difference between the CPPE and the one in barrier layers is that the former is non-barrier while the latter is barrier. However, they are similar in that in the first case the charge carriers are set in motion by the contact potential of the

Card 4/5

31)₁₂₇
B/502/60/008/000/001/003
Contact-potential photovoltaic ... D260/D304

electrodes, in the second case this is done by the potential difference at the contact between metal - semi-conductor. There are 6 figures and 31 references: 23 Soviet-bloc and 8 non-Soviet-bloc. The 4 most recent references to the English-language publications read as follows: Y. T. Sihvonen and D. R. Boyd: Ohmic probe contacts to CdS crystals, J. Appl. Phys., 29, (1958), 1143-1145; R.W. Smith, Properties of ohmic contacts to cadmium sulfide single crystals, Phys. Rev., 97, (1955), 1525-1530; Jan Tauc: Generation of an emf in semiconductors with non-equilibrium current carrier concentration. Rev. of Modern Physics, v. 29, 1957, p. 308-324; J.B. Kramer, Electrician, 93, 1924, 497.

SUBMITTED: October 10, 1959

Card 5/5

9,4179(1114,1137)

B/502/60/008/000/002/003 D260/D304

26.1512

AUTHORS:

Andreychin, R., and Fileva, N.

TITLE:

Transversal photovoltaic effect in evaporated layers

of silver sulphide

SOURCE:

Bulgarska akademiya na naukite. Fizicheski institut.

Izvestiya na fizicheskiya institut s ANEB, v. 8,

1960, 19-32

TEXT: The aim of the present exploratory work was to establish the universality of the transversal contact potential effect. Silver sulphide is a semiconductor with intereding photœlectric properties such as n-electron conductivity, presence of a barrier layer only several angstroms thick, anomalous direction of the rectified current, and ionic conductivity. The presence of a contact potential photovoltaic effect was observed in silver-sulphide elements which were obtained by the vacuum deposition of sulphur on a plate of silver. Two electrodes of different metals were deposited, one against another in the form of combs. The electromotive force apcard 1/4

31428 B/502/60/008/000/002/003 D260/D304

Transversal photovoltaic effect ...

pears as a result of the effect of light when the two electrodes are of different metals and a contact potential difference between them is established. Throughout all the experiments with photoelements the illumination was transversal, and uniform for the entire layer of the semiconductor. Polarity of the photoelectromotive force always followed the sign of the contact potential difference between the electrodes, when gold was the positive and aluminum the negative electrode. The majority of the photoelements showed an electromotive force of 5 to 300 millivolts in the dark and a current of 0.002 to 0.2 microamperes. The electromotive force increased by 20 to 30% in the light (values between 8 and 430 millivolts were observed) and the current then usually increased by a factor of two. The photovoltaic effect seems to possess considerable inertia. With some photoelements, when illuminated, there was a slow increase in the intensity of the current, while with others, there was first a decrease followed by an increase in the intensity of the current. When external tension was applied, the voltampere characteristics show ohmic contacts more seldom, and in most

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3址28 B/502/60/008/000/002/003 D260/D304

Transversal photovoltaic effect ...

cases the contacts are non-linear of the varistor type and are nearly always symmetrical or almost symmetrical. Instances of a non-typical rectifying effect with predominance in one direction are rare. Polarity of the photovoltaic effect was always the same, as determined by the contact potential difference between the electrodes, irrespective of the type of contacts and of the degree and direction of the rectifying effect. It was established that the observed photovoltaic effect is a contact-potential one and is independent of the type of contacts. The presence of the electromotive force and current in the dark is explained by the existence, to a greater or lesser extent, of ionic conductivity in the silver sulphide. Research in this connection is still continuing. The original paper also contains an explanation of certain anomalies observed in individual photoelements. G. Nadzhakov and R. Andreychin (Ref. 8: Izvestiya na BAN, seriya fizicheska, 2, no. 2, 1952, 1 - 4) are mentioned for their contribution in this field. There are 7 figures and 14 references: 12 Soviet-bloc and 2 non-Sovietbloc. The references to the English-language publications read as

Card 3/4

31128
B/502/6C/008/000/002/003
D260/D304
follows: J. Tauc, Rev. Mod. Physics 29, 308-324 (1957); M. H. Hebb,
Journ. Chem. Phys., 20, 185, (1952).

SUBMITTED: November 14, 1959

Card 4/4

s/058/61/000/012/032/083 A058/A101

AUTHORS:

Andreychin, R.. Kekhlibarov, T.

TITLE:

Small portable quartz spectrograph for measuring solar ultraviolet

radiation

PERIODICAL: Referativnyy zhurnal, Fizika, no. 12, 1961, 243, abstract 12G135

("Izv. fiz. in-t s ANYeB", 1960. no. 8, 267-274, Bulg., Russ. and

Germ. summaries)

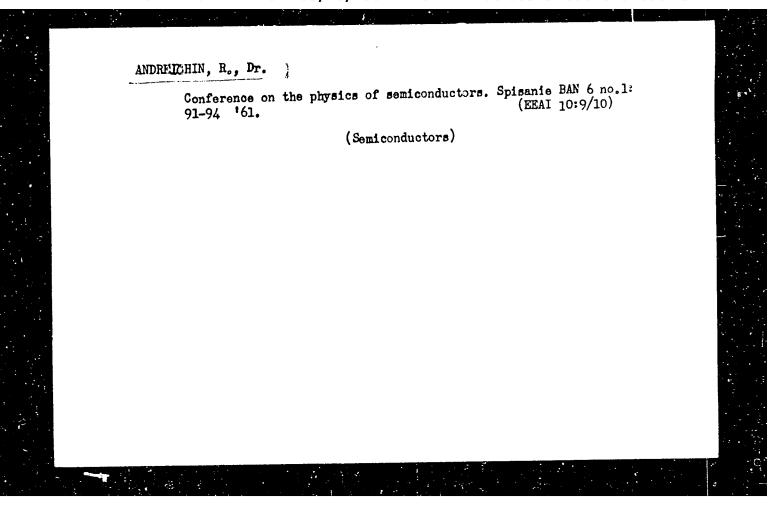
TEXT:

There is described a spectrograph using a self-collimating Ferri prism for comparative spectral intensity measurements of the Sun's ultraviolet

radiation.

[Abstracter's note: Complete translation]

Card 1/1



29,2400

S/181/62/004/003/040/045 B101/B102

AUTHORS:

Andreychin, R., and Kolomiyets, B. T.

TITLE:

The photo-electromotive force in arsenic chalcogenides

PERIODICAL: Fizika tverdogo tela, v. 4, no. 3, 1962, 814 - 815

TEXT: The dependence of photo-emf of the systems As₂S₃-As₂Se₃ and As₂Se₃-As₂Te₃ on their composition was examined. For this purpose a series of melts were studied in which sulphur was replaced by selenium and tellurium in increasing percentage: As₂S₃; 3As₂S₃·As₂Se₃; As₂Se₃; As₂Se₃;

The photo-electromotive force...

S/181/62/004/003/040/045 B101/B102

attended by a reduction in the photo-emf. The cause of the observed photo-emf is assumed to be either (a) a difference in the contact potentials, or (b) the presence of a barrier layer at the metal-semiconductor interface. The wide dispersion of the measured values despite the intensity of the illumination lends support to alternative (a) since the contact potential is strongly influenced by the surface of the specimen, made of applying the electrode, etc. This work was carried out jointly with the Institute of Physics of the Bulgarian As. There is 1 figure.

ASSOCIATION: Fiziko-tekhnicheskiy institut im. A. F. Ioffe AN SSSR, Leningrad (Physicotechnical Institute imeni A. F. Ioffe

of the AS USSR, Leningrad)

SUBMITTED:

December 30, 1961

Card 2/2

ANDREICHIN, R., d-r; MIKHAILOV, M.; NIKIFOROVA, M.

Independence of the contact-potential from the structural voltaic effect in thin layers of lead sulfide. Izv fiz atom BAN 9 no.2:5-16 '62.

1. Chlen na Redaktsionnata kolegiia, "Izvestiia na Fizicheskiia institut s ANEB" (for Andreichin).

NADZHAKOV, G., akad.; ANDREICHIN, R., d-r; BALABANOV, St.; STANISLAVOVA, IU.

Presence of a looking layer in the transversal photovoltaic effect in evaporated cadmium sulfide. Izv fiz atom BAN 9 no.2:17-23 '62.

1. Chlen na Redaktsionnata kolegiia i otgovoren redaktor, "Izvestiia na Fizicheskiia institut s ANEB" (for Nadzhakov). 2. Chlen na Redaktsionnata kolegiia, "Izvestiia na Fizicheskiia institut s ANEB" (for Andreichin).

NADZHAKOV, G., akad.; ANDREECHIN, R., d-r; STANISLAVOVA, IU.

Preliminary studies on the spectral distribution of the transversal photovoltaic effect in evaporated layers of cadmium sulfide. Izv fiz atom BAN 9 no.2:25-29 '62.

1. Chlen na Redaktsionnata kolegiia i otgovoren redaktor, "Izvestiia na Fizicheskiia institut s ANEB" (for Nadzhakov).

2. Chlen na Redaktsionnata kolegiia, "Izvestiia na Fizicheskiia institut s ANEB" (for Andreichin).

ANDREICHIN, R., d.-r; KEKHLIBAROV, T.

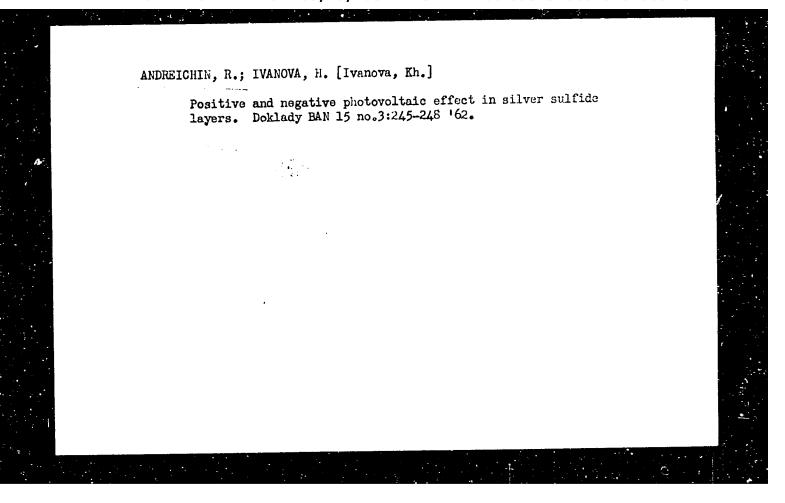
Comparative spectral measurements of the ultraviolet solar radiation. Pt. 1. 1960. Inv fix atom BAN 9 no.2:191-200 162.

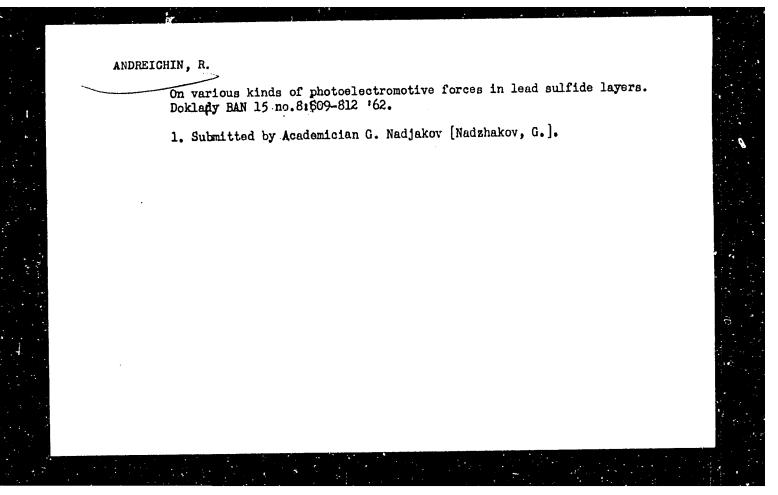
l. Chlen na Redaktsionmata kolegiia, "Izvestiia na Fizicheskiia institut s ANEB" (for Andreichin).

ANDREIGHIN, R., d-r; IVANOV, A., KEKHLISAROV, T.

A device for the standard development in the photographic photographic ctry. Tay fiz atom SAN 10 no.2:31-20 %2.

1. Ohlen na Redaktsionnata kolegiia, "Izvestiia na Fizicheskiia institut s ANSB."





ANDREICHIN, R : IVANOVA, H. [Ivanova, Nh.]

On photoelectromotive forces in crystal violet. Doklady BAN 15 no.8: 813-816 '63.

1. Submitted by Academician G. Nadjakov [Nadzhkov, G.].

Concerning the methods of determination of certain areas of electrical and photoelectric properties of semiconductors by means of measurement of contact potential differences. K. S. Balabanov (20 minutes).

Photovoltaic effects in CdS_Sel-x. R. Andreychin, A. Ivanov, M. Nikiforov, Yu. Stanislavova (20 minutes).

Report presented at the 3rd National Conference on Semiconductor Compounds, Kishinev, 16-21 Sept-1963

ANDIBICHIM

<u>L 18844-63</u>

EWP(q)/BDS AFFTC/ASD RDW/JD/JG

ACCESSION NR: AP3005932

g/0030/63/003/008/K280/K283

AUTHOR: Andrejtschin, R., Nikiforova, M., Ivanov, A., Stanislavova, J.

TITLE: Transverse photovoltaic effect in the CdS sub x Se sub (1-x) monocrystalline system (short note)

SOURCE: Physica status solidi, v. 3, no. 8, 1963, K280-K283

TOPIC TAGS: semiconductor, cadmium sulfide, cadmium selenide, cadmium sulfideselenide, photovoltaic effect, photoresistance, mixed semiconductor

ABSTRACT: CdS_xSe_(1-x) semiconductor system are solid solutions; capable of being prepared in many S:Se ratios. CdS, CdSe and mixed single crystals were prepared, employing the method described by N. I. Vitrichovskii and I. B. Mizebkaya; Fizika Tverdogo Tela, 1, 397 (1959), and examined as to their photovoltaic effect. The crystals were fastened to glass and placed between two electrodes (Al and/or Au; 0.8 to 1.0 millimeter apart) and vapor-treated. The gold electrode was rectifying and the aluminum electrode made ohmic contact as was expected. The photoelements thus prepared were illuminated perpendicular

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L 18844-63 ACCESSION NR: AP3005932

to the crystal plane and electrode surface. Elements with two identical electrodes (Al or Au) showed no photo-electromotive force; those containing one Al and one Au electrode did (200-4000 millivolt, the value depending on several factors), regardless of semi-conductor composition. The spectral dependence of the photovoltaic effect is shown in Figure 1, Enclosure 1. The relation between the long wavelength limit for the photovoltaic effect and semiconductor composition is shown in Figure 2, Enclosure 2. When used as photoresistor, the spectral distribution was of the usual type. Orig. art. has 3 figures.

ASSOCIATION: <u>Institute for Physics at the Bulgarian Academy of Sciences, Sofia</u> [Abstracter's note: original-language version not given]

SUBAITTED: 29Jun63

DATE ACQ: 26Aug63

ENCL: 02

SUB CODE: MA, PH

NO REF SOV: 002

OTHER: 000

Card 2/4

ANDREICHIN, R., d-r; KEKHLIBAROV, T.; MLADENOV, At.

A device for simultaneous recording of solar radiation intensity in various spectral regions. Izv fiz atom BAN ll no.1/2:49-58 163.

1. Chlen na Redaktsionnata kolegiia "Izvestiia na Fizicheskiia institut s ANEB" (for Andreichin).

ANDREICHIN R.

ACCESSION KR: AT4017774

B/2503/63/011/01-/0019/0029

AUTHOR: Andreychin, R.; Stanislavova, Yu.

TITLE: Photoelectromotive forces in evaporated CdS layers and mixed CdS-CdSe semiconductors

SCURCE: B"lgarska Akademiya na Naukite. Fizicheski institut. Izvestiya na Fizicheskiya institut s ANEB (News of the Institute of Physics and the Atomic Energy Scientific Research Foundation), v. 11, no. 1-2, 1963, 19-29

TOPIC TAGS: photovoltaic effect, photovoltaic, photoelectromotive force, semi-conductor, CdS, CdSe, In, Cu, Al, Au, photoelement, barrier layer, contact potential

ABSTRACT: Observations, made of the photovoltaic effect in $\mathrm{CdS}_{\mathbf{x}}\mathrm{Se}_{1-\mathbf{x}}$ evaporated layers (with all values of x from 1 to 0), supplement hitherto known instances of this phenomenon in CdS and CdSe. Layers were produced by evaporating in a vacuum substances of diverse origin, containing various quantities of activator impurities. Some layers were subjected to additional sensitization, and all to thermal treatment. Thermal treatment is not required to produce photoelectromotive force, but it heightens the mechanical strength of the layer. Applied to each layer -- likewise Card 1/1/3

ACCESSION NR: AT4017774

by evaporation in a vacuum -- were electrode pairs (In-Cu or Al-Au), spaced about 1 mm from each other. Under these conditions, all layers -- not only pure CdS or CdSe, but also mixed CdS_Se1-x layers -- exhibit a photovoltaic effect of an intensity which depends on the nature of the electrodes and the composition of the semiconductor. For CdS, photoelectromotive force amounts to as much as 400 millivolts with In-Cu electrodes, and 300 mV with Al-Au electrodes, while current (limited by the high internal resistance of the layers -- of the order of 102--100 ohms) amounts to as much as 50 microamperes. As the S is gradually replaced with Se until pure CaSe is obtained, the intensity of the e.m.f. manifests a tendency gradually to decrease, while current, conversely, tends to increase (up to 200 mA in the case of CdSe). In all cases Cu or Au is the positive pole in the external circuit of the photoelement. Usually the intensity of e.m.f. is lower after the electrodes are placed on the layer, but increases in the course of time, attaining the values mentioned above. The authors compared these facts with the curve of values of photoelectromotive force appearing when various sites of the semiconductor layer were illuminated with a narrow beam of light (Fig. 1 of the Enclosure), and concluded that two effects occur here simultaneously, viz: the photovoltaic effect of a barrier layer and a contact potential photovoltaic effect. In time the component of the former increases, probably by reason of the adsorption of gases as it shifts to the copper or gold electrode. The spectral distribution of

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ACCESSION NR: AT4017774

the effect depends on the composition of the layer and its impurities. Maximum sensitivity gradually shifts from about 500 nm for CdSe to more than 700 nm for CdSe. For semiconductor layers without an activator the curves are comparatively narrow (Fig. 3, for CdS), while with an increase in the quantity of activator impurities they become wider (Fig. 2 for CdS, Fig. 4 for CdSo.15Seo.85 and Fig. 5 for CdSe), with sensitivity continuing quite far toward the long wave end. When the same layers function as photoresistors, the spectral sensitivity curve is much narrower and is significantly displaced toward the end with shorter waves (Figs. 2 and 4 of the Enclosure). "The authors express their gratitude to Comrade M. Nikiforova for the production and chemical treatment of basic substances." Orig.

ASSOCIATION: none

SUBMITTED: 02Mar63

art. has: 5 figures.

DATE ACQ: 04Mar64

ENCL: 04

SUB CODE: PH

NO REF SOV: 004

OTHER: 010

Card 3/13

ACCESSION NR: AT4017775

B/2503/63/011/01-/0031/0037

AUTHOR: Andreychin, R.; Nikiforova, M.; Ivanov, A.; Stanislavova, M.

TITLE: Transversal photovoltaic effect in mixed CdS-CdSe crystals

SOURCE: B"lgarska Akademiya na Naukite. Fizicheski institut. Izvestiya na Fizicheskiya institut s ANEB (News of the Institute of Physics and the Atomic Energy Scientific Research Foundation), v. 11, no. 1-2, 1963, 31-37

TOPIC TAGS: CdS, CdSe, mixed crystal, crystal, photovoltaic effect

ABSTRACT: Mixed CdS_XSe_{l-X} single crystals with values of x from 0 to 1 were produced by evaporating a mixture of powdered CdS and CdSe and recrystallizing it by the method described by Vitrikhovskiy and Mizetskaya (FTT (Solid State Physics), 1, 397-402, 1952). These crystals represented a continuous series of solid colutions of replacement, with any given sulfur-selenium ratio falling within the limits of stoichiometric composition. The composition of the crystals was determined by means of preliminary calculation of the components and verified by direct chemical analysis of finished crystals. Crystals were glued to glass plates and a pair of metal electrodes applied to them by evaporation in a vacuum. These electrodes were parallel to each other and spaced about 1 mm from each other (Figure 1 of the Enclosure).

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When electrodes of different metals (Al-Au or In-Cu) were applied to the crystals. under illumination there originated an electromotive force of the order of 200 to 400 millivolts, and a current with density from 100 to 200 microamperes per centimeter of semiconductor-electrode contact. (In this connection, only semi-conductorgold or semi-conductor-copper electrode is active here; illumination of the other electrode of the free surface of the crystal between electrodes has no material significance.) The value of e.m.f. apparently is greatest in the case of CdS and diminishes with an increase in the content of selenium in mixed semiconductors. The spectral distribution of this photovoltaic effect is quite characteristic. Its curve in the case of wave lengths shorter than 400-450 nm has not been completely explained, but from this point to the adsorption face of the crystal (scaled per unit of incident light energy) remains the same for any wave length (Figure 2 of the Enclosure). Long-wave sensitivity limit, corresponding to the adsorption face, varies smoothly with the composition of crystals from 500 nm in the case of CdS to 740 nm in the case of CdSe (Figure 3 of the Enclosure). If we apply an external field and test these photoelements as photoresistances, the spectral distribution for these same crystals is typical of photoconductivity, even when different electrodes are used (Fig. 4 of the Enclosure). The authors believe that the effect is purely superficial rather than deepseated, and further investigation is in progress to elucidate not only the properties, but also the character of the effect. Orig.

Card 2/6 ?

ACCESSION NR: AT4017775

art. has 4 figures.

ASSOCIATION: none

SUBMITTED: 02Mar63

SUB CODE: PH, GE

DATE ACQ: 04Mar64

NO REF SOV: OOL

ENCL: 03

OTHER: 018

Card 3/4 3

ANDREICHIN, R., d-r; STANISLAVOVA, IU.

Photoelectromotive forces in evaporated calmium sulfide layers and mixed cadmium sulfide and cadmium selenide semiconductors. Izv fiz atom BAN 11 no.1/2:19-29 *63.

1. Chlen na Redaktsionnata kolegiia, "Izvestiia na Fizicheskiia institut s ANEB" (for Andreichin).

ANDREICHIN, R., d-r; NIKIFOROVA, M.; IVANOV, A.; STANISLAVOVA, IU.

Transversal photovoltaic effect in mixed cadmium sulfide and cadmium selenide crystals. Izv fiz atom BAN 11 no.1/2:31-37 '63.

1. Chlen na Redaktsionnata kolegiia, "Izvestiia na Fizicheskiia institut s ANEB" (for Andreichin).

ANDREICHIN, Razum, prof. d-r

Fluorescent or luminescent lamps. Elektroenergiia 15 no.4:31
Ap '64.

l. Institute of Physics and Atomic Research Laboratory, ${}^{\underline{B}}\!\!$ ulgarian Academy of Sciences.

IJP(c) EWT(1) AT L 11121-66 ACC NR: AP6001077 SOURCE CODE: BU/0011/65/018/010/0903/0905 44,55 44,55 44,55 AUTHOR: Kandilarov, B.; Stanislavova, Andreichin, R. ORG: Institute of Physics, Bulgarian Academy of Science 21,44,55 TITLE: Spectral sensitivity of CdS+CdSe heterojunction photovoltaic effect and some problems of quasiepitaxy SOURCE: Bulgarska akademiya na naukite. Doklady, v. 18, no. 10, 1965, 903-905 TOPIC TAGS: pn junction, photoelectric cell, photoelectric effect, cadmium sulfide, cadmium selenide ABSTRACT: Changes in the spectral dependence of the heterojunction photovoltaic effect arising because of the structural differences of the two contacting substances were investigated in CdS-CdSe photoelements. Tests of variously treated glass substrates showed that the largest photovoltages are obtained when the semiconductors are deposited on a smooth glass plate and when this substrate is heated during the deposition of the bottom electrode. In some cases good photoelements were also obtained on finely matted and preheated glass plates. It is suggested that in the process of heating, structural changes occur in the CdS layer and in the intergrowth between the two surfaces, without affecting the long-wave sensitivity of the CdSe upper layer. Orig. art. has: 4 figures. SUB CODE: 1.0/, SUBM DATE: none/ OTH REF: 002/ ATD PRESS: 4/76

APPROVED FOR RELEASE: 03/20/2001 CIA-RDP86-00513R000101510004-9"

Card 1/1

L 34516-66 IJP(c) EVT(1)SOURCE CODE: BU/0011/65/018/010/0903/0905 ACC NR: AP6024740 36 AUTIOR: Kandilarov, B.; Stanislavova, Y.; Andreichin, R. B ORG: Institute of Physics, BAIL TITLE: Spectral sensitivity of CdS-CdSe heterojunction photovoltaic effect and some problems of quasiepitaxy SOURCE: Bulgarska akademiya na naukite. Doklady, v. 18, no. 10, 1965, 903-905 TOPIC TAGS: photovoltaic effect, spectrum analysis, cadmium compound The authors reported in an earlier paper (Phys.: ABST: ACT: Stat. Sol., 8, 1765, 897) the observations of the photovoltaic effect of the CdS-CdSe heterojunction. The present paper describes changes in the spectral dependence of this photovoltaic effect caused by the differences in structure of the two substances in contact. Results show that whenever a process of major importance (like the photovoltaic effect) occurs in the heterojunction ragion, the spectral distributions of the photoeffect for epitexial and quasispitaxial heterojunction appear the more similar the more completely the region of structurel matching encompasses the region of heterojunction, i.e., the closer its structure comes to an ordinary epitaxial junction. This paper was presented by Academician G. Nadjakov on 5 July 1965. Orig. art. has: 6 figures. [Orig. art. in Eng.] [JPRS: 34.789]
SUB CODE: 20 | SUBM DATE: none | OTH REF: 005 SUB CODE: Card 1/1 1/0 Q 25 70 1010

ANDREICOVICI, Gh., ing. Methods of analyzing and identifying polynitrilacrylic and polyesteric fibers. Ind text Rum 13 no.1:40-43 Ja 162 1. Institutul de cercetari textile.

AVACHIAN, A., ing.; ANDREICOVICI, G., ing.

Stability of the white color and its determination on cotton fabrics. Ind text Rum 13 no.12:509-511 D '62.

1. Institutul de cercetari textile.

DANATIBL, C., ing.; MARGU, Gh., Ang; IGLACCE, Gh.; MARC, E.; PATEL, I.

VASHLEGGE, F., ing.; ROGE, A., ing.; PATEL, E., ing.; PATEL, A.;

MHAI, Gh.; SAMPULASCE, F., ing.; AVACEDAR, A., ing.; AMERICANEL,
Gh., ing.; UNDERFREGEE, E., ing.

New technology in corbed cetten spinning for improving yarn
quality. Ind text Num 14 no.10:448-450 S 163.

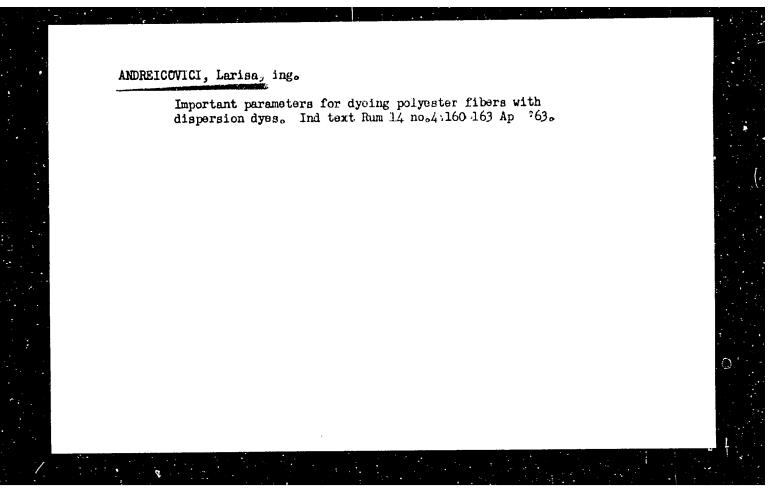
1. Do la Filatura resimenanca de bumbac (for Famaitide, Pareu,
Jonescu, Radu, Favel, F., Vasilescu, Ropu, Pavel, M., Enedi,
Mihai, Sandilescu).

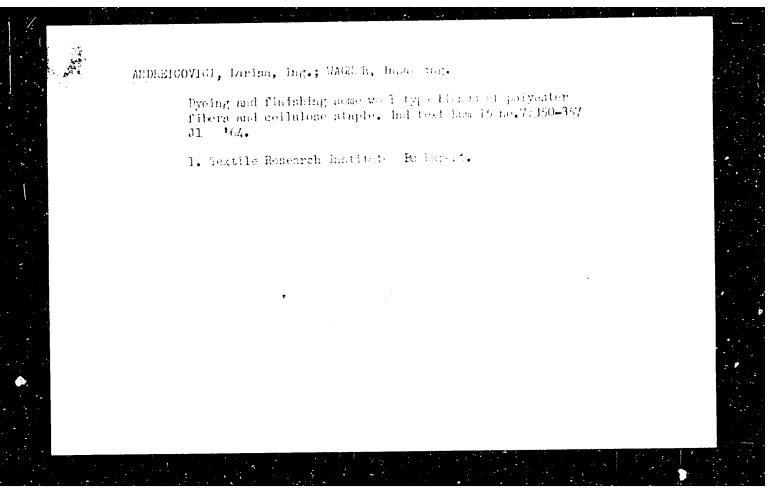
2. De la Institutul de cercetari textile (for Avachian,
Andreicovici, Unterfinger).

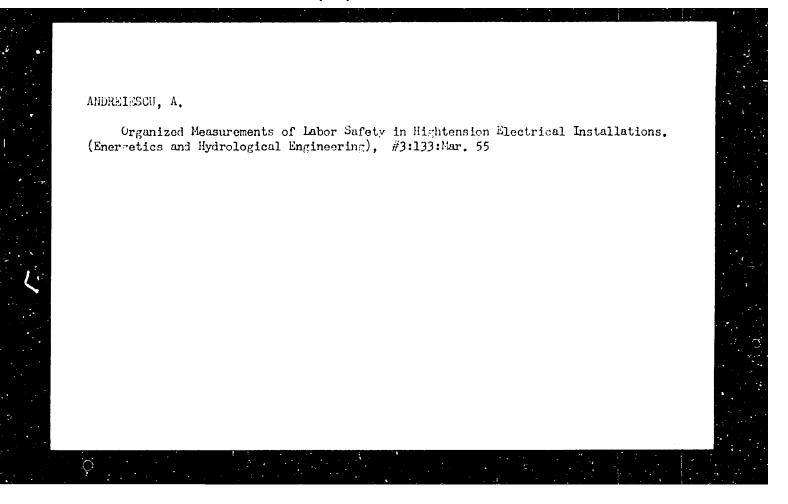
ANDREICOVICI, Ch., ing.; GHEORGHE, A.

Methods for obtaining microscopic sections of textile
fibers of 10-15 microns thick and their photographing.

Ind text Rum no. 3: 151-156 Mr '64.







AVARHIAN, A. [Avahian, A.], inzh.; ANDREIKOVICHI, G. [Andreicovici, G], inzh.

Whiteness stability and its determination in cotton fabrics. Tekstilna prom 12 no.5:18-19'63.

1. Nauchnoizsledovatelski institut po tekstila, RNR.

"Twenty-two Spartak automobiles' worth in gold."

p. 9 (Ceskoslovensky Vojak) Vol. 6, no. 25, Dec. 1957
Prague, Czechoslovakia

SO: Monthly Index of East European Accessions (EEAI) LC. Vol. 7, no. 4,
April 1958

ANDREJCIC, R.

Seminar on the modern methods of quality control. p. 317.

Periodical: NOVA PROIZVODNJA.

Vol. 9, no. 4/6, 1958.

TECHNOLOGY

SO: Monthly List of East European Accessions (EEAI) LC

Vol. 8, No. 4 April 1959, Uncl.

ANDREJCIC, R.

How to use binomial graph paper for checking defects. p. 341.

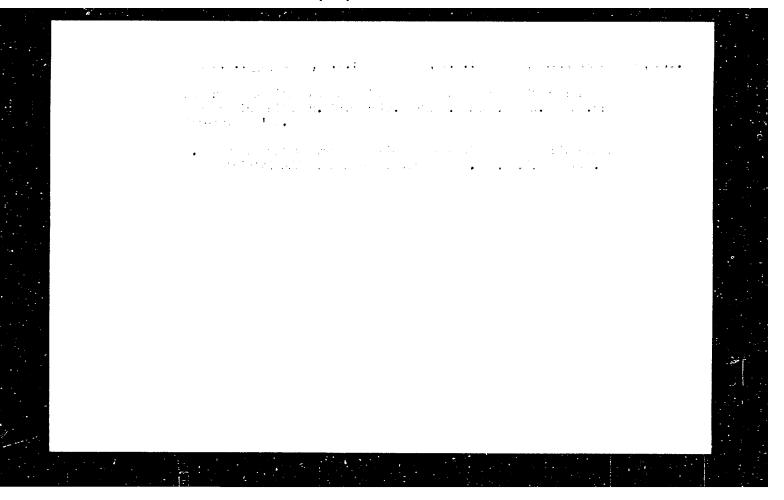
Periodical: NOVA PROIZVODNJA.

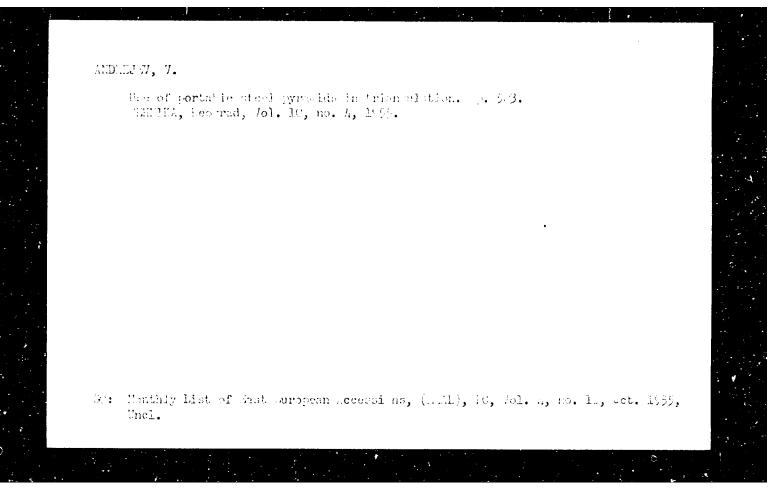
Vol. 9, no. 4/6, 1958.

TECHNOLOGY

SO: Monthly List of East European Accessions (EEAI) LC

Vol. 8, No. 4 April 1959, Uncl.





Enterpley, V. Lathed of initial parameters in station is lease. p.1002

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